

L Number	Hits	Search Text	DB	Time stamp
-	26372	gate near electrode\$1 and polysilicon	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/21 10:38
-	25	(gate near electrode\$1 and polysilicon) and polish\$3 near5 silicide	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/02 10:47
-	11	("5683941" "5770507" "5817562" "5824588" "5904533" "5953614" "5985768" "6001721" "6013569" "6072222" "6074921" "9084280").PN.	USPAT	2003/07/02 10:25
-	32	("4514233" "4577392" "4616401" "4803173" "4826781" "4829025" "4935376" "4948745" "4992388" "5045483" "5168072" "5268330" "5306665" "5310692" "5366911" "5391510" "5411909" "5429987" "5434093" "5447875" "5496771" "5516716" "5545579" "5585661" "5610083" "5633187" "5656519" "5683941" "5731239" "5780349" "5843834" "5953612").PN.	USPAT	2003/07/02 10:30
-	17	("4514233" "4803173" "4935376" "5268330" "5310692" "5366911" "5411909" "5434093" "5447875" "5496771" "5516716" "5545579" "5585661" "5610083" "5633187" "5683941" "5843834").PN.	USPAT	2003/07/02 10:32
-	18	("4518629" "4587718" "4690730" "4740484" "4746219" "4753709" "4755478" "4795722" "4824521" "4849369" "4877775" "4966870" "4994402" "5013678" "5022958" "5034348" "5081065" "5086017").PN.	USPAT	2003/07/02 10:35
-	11	("4545116" "4575920" "4622735" "4755478" "4795722" "4822754" "4859278" "4914500" "4933297" "4965226" "5023204").PN.	USPAT	2003/07/02 10:35
-	12	("4807007" "4984042" "5200352" "5391510" "5532181" "5668035" "5904508" "6033958" "6037201" "6037222" "6040222" "6040610").PN.	USPAT	2003/07/02 10:45
-	8085	438/299,592,301,305,306,307,595,706,720,721, USPAT93.ccls	USPAT93.ccls	2003/07/02 10:48
-	3107	438/299,592,301,305,306,307,595,706,720,721, and gate near electrode\$1	USPAT93.ccls	2003/07/02 10:48
-	9	(438/299,592,301,305,306,307,595,706,720,721, and gate near electrode\$1) and polish\$3 near5 silicide\$1	USPAT93.ccls	2003/07/02 10:49
-	453	polish\$3 near3 rate same dish\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/21 10:47
-	422	(polish\$3 near3 rate same dish\$3) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/21 10:48
-	40	polish\$3 near3 rate same etch\$3 near2 stop	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/21 10:48

-	38	(polish\$3 near3 rate same etch\$3 near2 stop) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/21 10:48
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